

IN THE CLAIMS

1. (Currently amended) A method of fabricating a semiconductor device comprising:
 - providing a substrate having at least one semiconductor layer;
 - forming a conductive layer over the substrate;
 - vapor priming a first silicon-containing material over [[the]] a gate oxide;
 - vapor priming a second silicon-containing material over the first silicon-containing material;
 - forming a silicon-containing dielectric layer having a thickness of about 35Å by processing the first silicon-containing material and the second silicon-containing material with a reactive agent selected to react with silicon atoms of the first silicon-containing material and the second silicon-containing material; and
 - forming a gate electrode over the silicon-containing dielectric layer.
2. (Original) The method of claim 1 further comprising:
 - doping the gate electrode with phosphor.
3. (Original) The method of claim 1 further comprising:
 - doping the gate electrode with boron.
4. (Original) The method of claim 1 wherein processing the silicon-containing material in a reactive ambient comprises rapid thermally nitridizing the silicon-containing material in an NH₃ ambient at a processing temperature of 850°C.